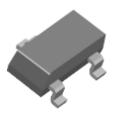
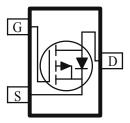
P-Channel 20-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

- Low r_{DS(on)} provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe SC70-3 saves board space
- Fast switching speed
- High performance trench technology

PRODUCT SUMMARY				
V _{DS} (V)	r _{DS(on)} (OHM)	ID (A)		
-20	$0.079 @V_{CS} = -4.5V$	-1.7		
	$0.110@V_{CS} = -2.5V$	-1.5		





ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Maximum	Units			
Drain-Source Voltage			-20	v		
Gate-Source Voltage	Voltage			v		
Cartingan Daris Connect ^a	$T_A=25^{\circ}C$	т_	-1.7			
Continuous Drain Current ^a	T _A =25°C T _A =70°C	Ъ	-1.4	Α		
Pulsed Drain Current ^b	n Current ^b		-2.5			
Continuous Source Current (Diode Conduction) ^a			±0.28	Α		
D	$T_A=25^{\circ}C$	D.	0.34	w		
Power Dissipation ^a	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	1 D	0.22	vv		
Operating Junction and Storage Temperature Range		TJ, Tstg	-55 to 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
	$t \ll 5 \sec$	D	375	⁰ CM1		
Maximum Junction-to-Ambient ^a	Steady-State	R _{THJA}	430	Ċw		

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

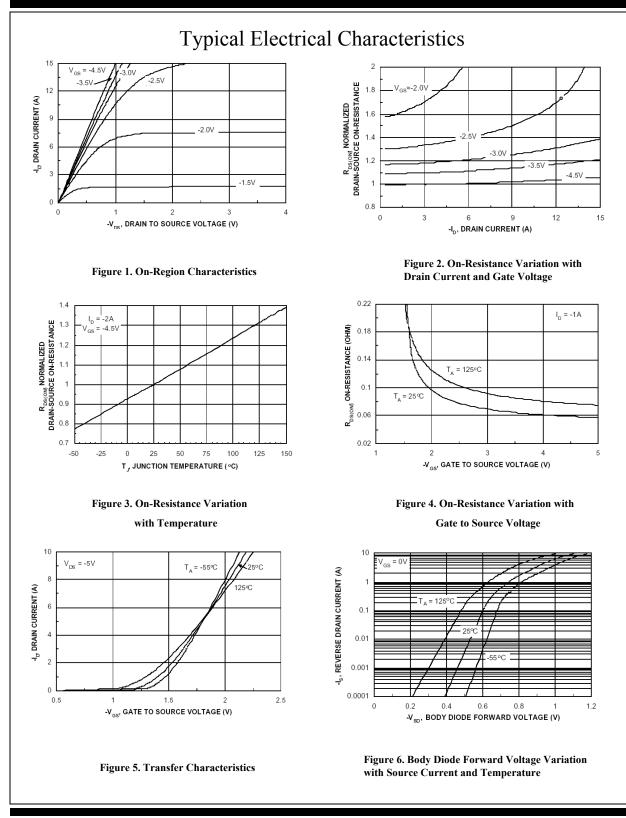
SPECIFICATIONS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Test Conditions	Limits			TL. 4	
rarameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static			-			-	
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -250 \text{ uA}$	-0.4			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 8 V$			±100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -16 V, V_{GS} = 0 V$			-1	uA	
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}, T_J = 55^{\circ}\text{C}$			-10		
On-State Drain Current ^A	I _{D(on)}	$V_{DS} = -5 V$, $V_{GS} = -4.5 V$	-5			А	
Drain-Source On-Resistance ^A		$V_{GS} = -4.5 \text{ V}, I_D = -1.7 \text{ A}$			79	mΩ	
Drain-Source On-Resistance	r _{DS(on)}	$V_{GS} = -2.5 \text{ V}, I_D = -1.5 \text{ A}$			110		
Forward Tranconductance ^A	$g_{\rm fs}$	$V_{DS} = -5 V$, $I_D = -1.25 A$		9		S	
Diode Forward Voltage	V _{SD}	$I_{\rm S}$ = -0.46 A, $V_{\rm GS}$ = 0 V		-0.65		V	
Dynamic ^b							
Total Gate Charge	Qg	$V_{DS} = -10 V, V_{GS} = -4.5 V,$		7.2			
Gate-Source Charge	Q _{gs}	$v_{\rm DS} = -10 v, v_{\rm GS} = -4.3 v,$ $I_{\rm D} = -1.7 {\rm A}$		1.7		nC	
Gate-Drain Charge	Q _{gd}	$I_{\rm D} = -1.7$ A		1.5			
Turn-On Delay Time	t _{d(on)}			10			
Rise Time	t _r	$V_{DD} = -10 \text{ V}, \text{ I}_{L} = -1 \text{ A},$		9		ns	
Turn-Off Delay Time	t _{d(off)}	V_{GEN} = -4.5 V, R_G = 6 Ω		27		115	
Fall-Time	t _f			11			

Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.
- c. Repetitive rating, pulse width limited by junction temperature.

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f = 1 MHz V_{GS} = 0 V

20

15

Typical Electrical Characteristics 1000 = -3.5A -5\ I, 10V 68, GATE-SOURCE VOLTAGE (V) Ciss 800 15 CAPACITANCE (pF) 3 600 2 400 Coss 1 200 7 0 0 0 2 8 1 3 4 5 6 7 9 0 5 10 Q d GATE CHARGE (nC) -VDS, DRAIN TO SOURCE VOLTAGE (V) Figure 7. Gate Charge Characteristic Figure 8. Capacitance Characteristic 100 5 LIMIT Re

100µs

10

l0m•

-VDS, DRAIN-SOURCE VOLTAGE (V)

.

V_{GS} = -4.5V

SINGLE PULSE R_{9JA} = 156°C/W $T_A = 25^{\circ}C$

1

Figure 9. Maximum Safe Operating Area

-In. DRAIN CURRENT (A)

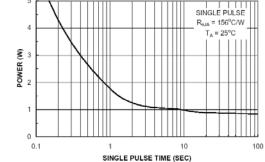
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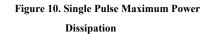
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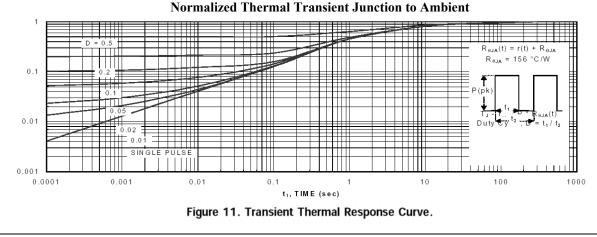
0.1

0.01

0.1





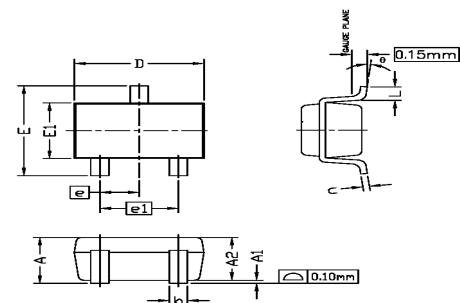


Normalized Thermal Transient Junction to Ambient

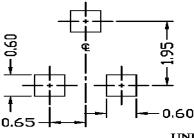
100

Package Information

SC70 PACKAGE OUTLINE



RECOMMENDED LAND PATTERN



SYMBOLS	DIMENSIONS IN MILLIMBTERS		DIMENSIONS IN INCHES			
a 1 MISULA	MIN	NOM	MAX	MIN	NOM	MAX
Α			1.10			0.043
A1	0.00		0.10	0.00		0.004
A2	0.7	0.9	1.00	0.028	0.035	0.039
ь	0.15		0.30	0.006		0.012
c	0.08		0.22	0.003		0.009
D	1.85	2.10	2,15	0.073	0.083	0.085
Е	1.80	2.30	2.40	0.071	0.091	0.094
e	0.65 BSC				0.026 BSC	
el	1.30 BSC				0.051 BSC	
E 1	1.1	1.30	1.4	0.043	0.051	0.055
L	0.26	0.36	0.46	0.010	0.014	0.018
Ð	0°	4°	8°	0°	4°	8°

UNIT: mm

NOTE

- 1. ALL DIMENSIONS ARE IN MILLMETERS.
- 2. DIMENSIONS ARE INCLUSIVE OF PLATING.
- 3. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
- MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 3 MILS EACH.
- 4. DIE IS FACING UP FOR MOLD AND FACING DOWN FOR TRIM/FORM. ie:REVERSE TRIM/FORM.
- 5. DIMENSION L IS MEASURED IN GAUGE PLANE.
- 6. CONTROLLING DIMENSION IS MILLIMETER. CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.